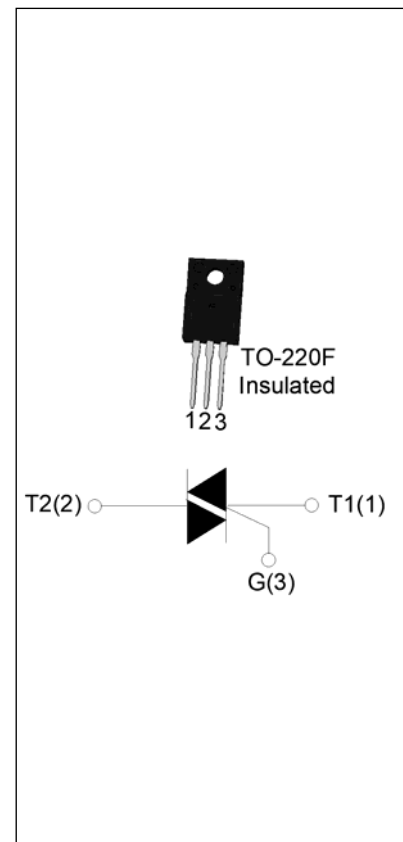


T1220H-6F 12A TRIAC

Rev.A.1.1

DESCRIPTION:

The T1220H-6F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T1220H-6F provides a very high switching capability up to junction temperatures of 150°C. By using an external plastic package, T1220H-6F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III}$	20/20/20	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 106^{\circ}C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		132	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	72	A ² s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=150^{\circ}C$)	di/dt	100	A/ μs
Peak gate current ($t_p=20\mu s$, $T_j=150^{\circ}C$)	I_{GM}	4	A

Average gate power dissipation ($T_j=150^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX.	20	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	25	mA
		II		55	
I_H	$I_T=500\text{mA}$		MAX.	25	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=150^{\circ}\text{C}$		MIN.	500	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20\text{V}/\mu\text{s}$, $T_j=150^{\circ}\text{C}$		MIN.	3	A/ms
t_{on}	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	3	μs
t_{off}				60	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=17\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^{\circ}\text{C}$	0.75	V
R_D	Dynamic resistance	$T_j=150^{\circ}\text{C}$	37	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=150^{\circ}\text{C}$	1.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.8	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

T	12	20	H	-6	F
Triacs	$I_{T(RMS)}:12A$	$20:I_{GT1-3}\leq 20mA$		$6:V_{DRM}/V_{RRM}\geq 600V$	F:TO-220F(Ins)
			High junction temperature		

MARKING

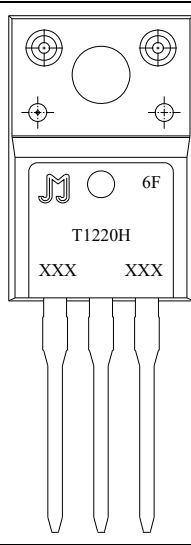
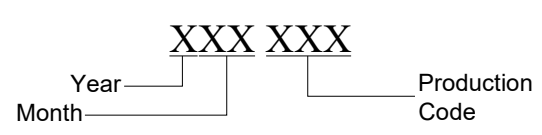
	
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FIG.1: Maximum power dissipation versus RMS on-state current

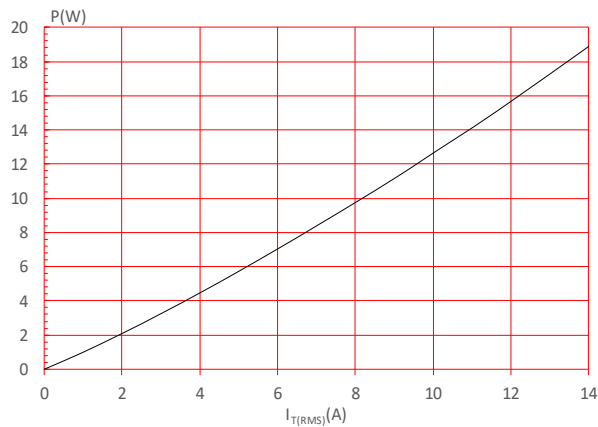


FIG.3: Surge peak on-state current versus number of cycles

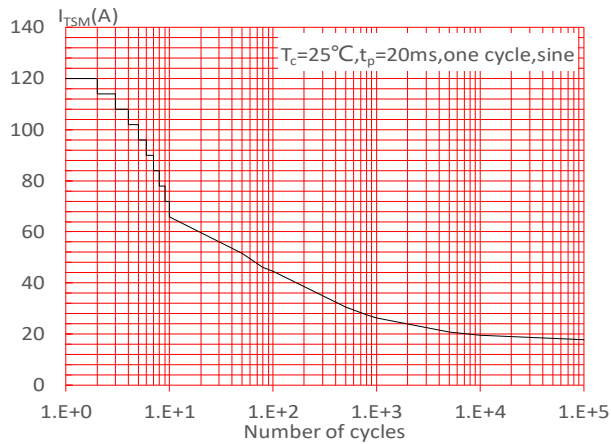


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

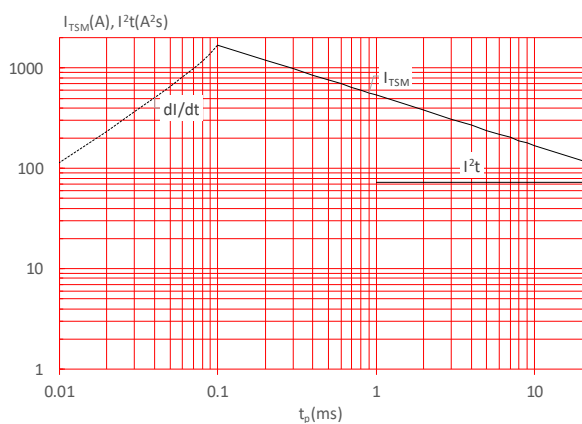


FIG.2: RMS on-state current versus case temperature

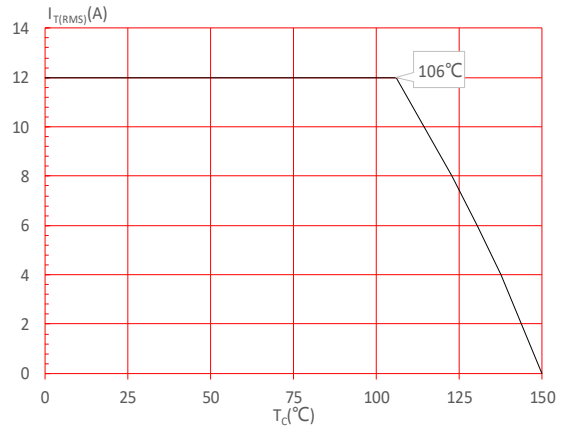


FIG.4: On-state characteristics

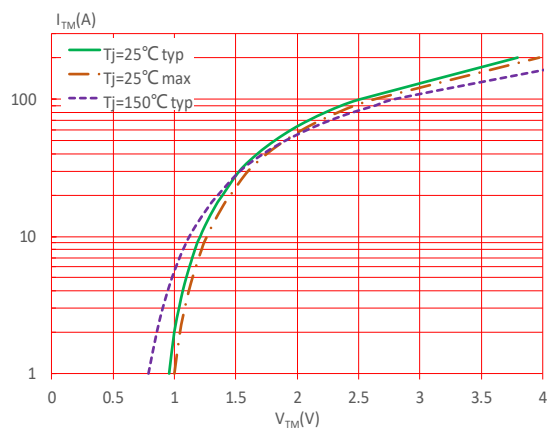


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

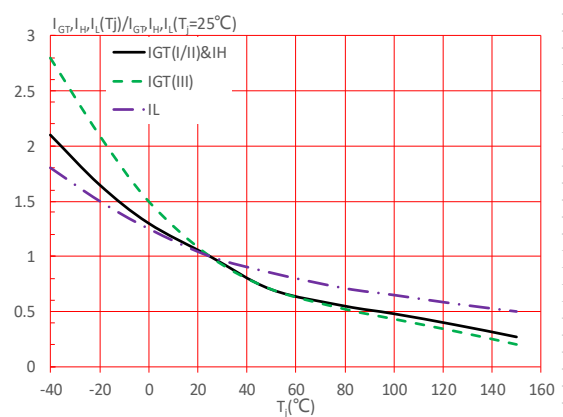
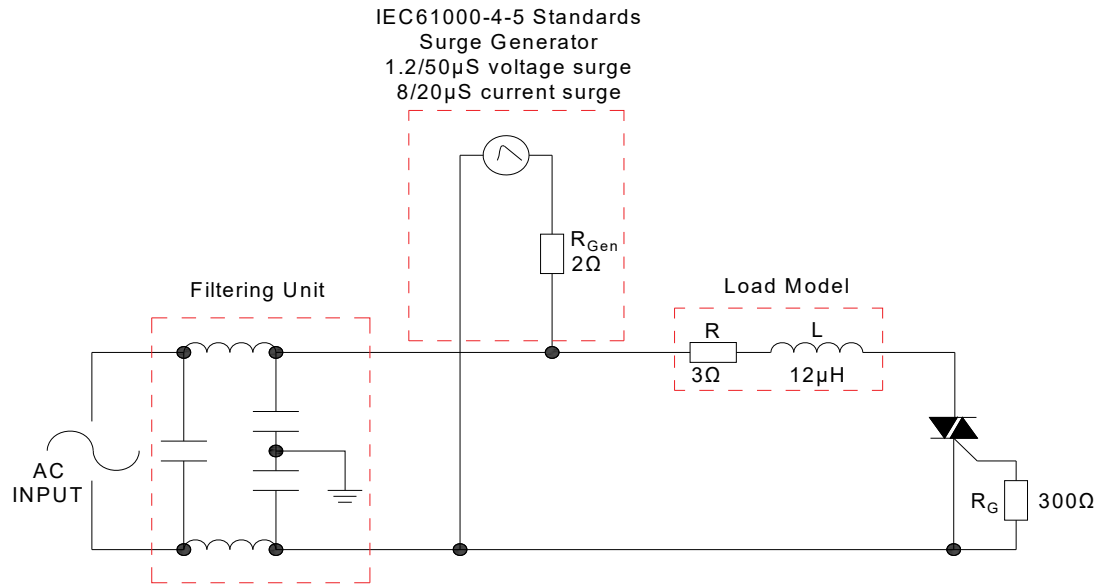


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
T1220H-6F	600	20	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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